VN2410

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- Free from Secondary Breakdown
- Low Power Drive Requirement
- Ease of Paralleling
- Low C_{ISS} and Fast Switching Speeds
- Excellent Thermal Stability
- Integral Source-Drain Diode
- High Input Impedance and High Gain

Applications

- Motor Controls
- Converters
- Amplifiers
- Switches
- Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

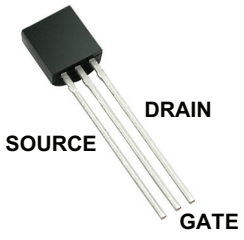
General Description

The VN2410 Enhancement-mode (normally-off) transistors use a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited for a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Type

3-lead TO-92
(Top view)



See Table 2-1 for pin information.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-Source Voltage ..... BV_{DSS}
Drain-to-Gate Voltage ..... BV_{DGS}
Gate-to-Source Voltage ..... ±20V
Operating Ambient Temperature, T_A ..... –55°C to +150°C
Storage Temperature, T_S ..... –55°C to +150°C

† Notice: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	240	—	—	V	V_{GS} = 0V, I_D = 100 µA
Gate Threshold Voltage	$V_{GS(th)}$	0.8	—	2	V	V_{GS} = V_{DS}, I_D = 1 mA
Gate Body Leakage Current	I_{GSS}	—	—	100	nA	V_{GS} = 20V, V_{DS} = 0V
Zero-Gate Voltage Drain Current	I_{DSS}	—	—	10	µA	V_{GS} = 0V, V_{DS} = 120V
		—	—	500	µA	V_{GS} = 0V, V_{DS} = 120V, T_A = 125°C (**Note 1**)
On-State Drain Current	$I_{D(ON)}$	1	—	—	A	V_{GS} = 10V, V_{DS} = 15V
Static Drain-to-Source On-State Resistance	$R_{DS(ON)}$	—	—	10	Ω	V_{GS} = 2.5V, I_D = 100 mA
		—	—	10	Ω	V_{GS} = 10V, I_D = 500 mA
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	1	1.4	%/°C	V_{GS} = 10V, I_D = 500 mA (**Note 1**)

Note 1: Specification is obtained by characterization and is not 100% tested.

AC ELECTRICAL CHARACTERISTICS

Electrical Specifications: T_A = 25°C unless otherwise specified. All AC parameters are not 100% sample tested.						
Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
Forward Transconductance	G_{FS}	300	—	—	mmho	V_{DS} = 10V, I_D = 500 mA
Input Capacitance	C_{ISS}	—	—	125	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1 MHz
Common-Source Output Capacitance	C_{OSS}	—	—	50	pF	
Reverse Transfer Capacitance	C_{RSS}	—	—	20	pF	
Turn-On Delay Time	$t_{d(ON)}$	—	—	8	ns	V_{DD} = 60V, I_D = 400 mA, R_{GEN} = 25Ω
Rise Time	t_r	—	—	8	ns	
Turn-Off Delay Time	$t_{d(OFF)}$	—	—	23	ns	
Fall Time	t_f	—	—	24	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V_{SD}	—	1.2	—	V	V_{GS} = 0V, I_{SD} = 190 mA (**Note 1**)

Note 1: Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 µs pulse, 2% duty cycle

TEMPERATURE SPECIFICATIONS

Parameter	**Sym.**	**Min.**	**Typ.**	**Max.**	**Unit**	**Conditions**
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	–55	—	+150	°C	
Storage Temperature	T_S	–55	—	+150	°C	
PACKAGE THERMAL RESISTANCE						
3-lead TO-92	θ_{JA}	—	132	—	°C/W	

THERMAL CHARACTERISTICS

Package	**I_D (Note 1) (Continuous) (mA)**	**I_D (Pulsed) (A)**	**Power Dissipation at T_A = 25°C (W)**	**I_{DR} (Note 1) (mA)**	**I_{DRM} (A)**
3-lead TO-92	190	1.7	1	190	1.7

Note 1: I_D (continuous) is limited by maximum rated T_J.

2.0 PIN DESCRIPTION

The details on the pins of VN2410 are listed in Table 2-1. Refer to **Package Type** for the location of pins.

TABLE 2-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	Source	Source
2	Gate	Gate
3	Drain	Drain

3.0 FUNCTIONAL DESCRIPTION

Figure 3-1 illustrates the switching waveforms and test circuit for VN2410.

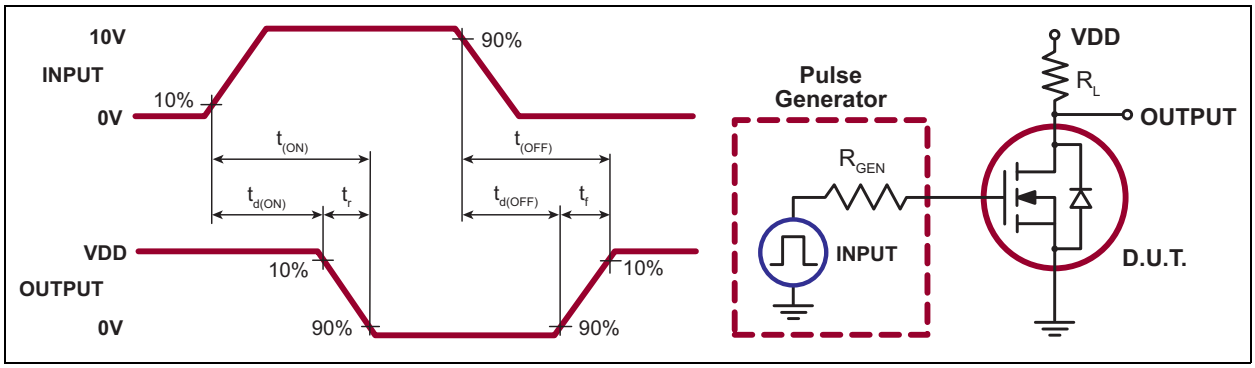


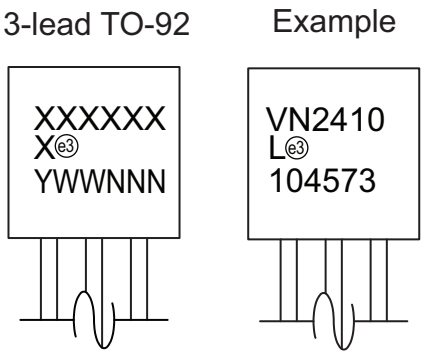
FIGURE 3-1: *Switching Waveforms and Test Circuit.*

TABLE 3-1: PRODUCT SUMMARY

BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (Maximum) (Ω)	I_{DSS} (Minimum) (A)
240	10	1

4.0 PACKAGING INFORMATION

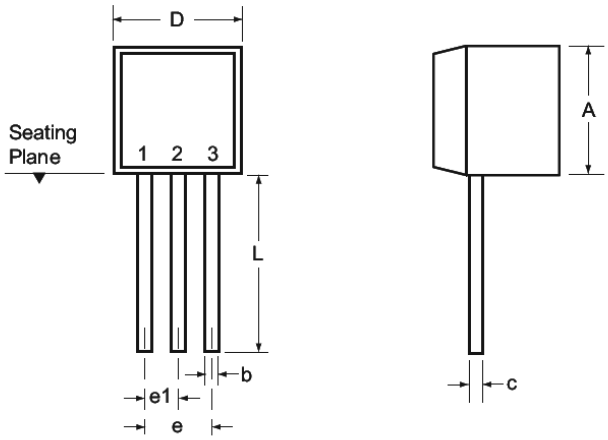
4.1 Package Marking Information



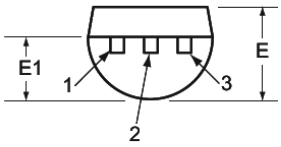
Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

3-Lead TO-92 Package Outline (L/LL/N3)



Front View **Side View**



Bottom View

Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the JEDEC drawing.*
† This dimension differs from the JEDEC drawing.
Drawings not to scale.

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (May 2021)

- Converted and merged Supertex Doc# DSFP-VN2410 to Microchip DS20006534A
- Changed the package marking format
- Removed 3-lead TO-92 L P002, P003, and P005 media types to align packaging specifications with the actual BQM
- Added section(s) to comply with Microchip formatting standards
- Made minor text changes throughout the document

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	XX	-	X	-	X
Device	Package Options		Environmental		Media Type

Device:	VN2410	=	N-Channel Enhancement-Mode Vertical DMOS FET
Package:	L	=	3-lead TO-92
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package
Media Types:	(blank)	=	1000/Bag for an L Package
	P013	=	2000/AMMO Pack for an L Package
	P014	=	2000/AMMO Pack for an L Package

Examples:

a) VN2410L-G:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 1000/Bag
b) VN2410L-G-P013:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 2000/AMMO Pack
c) VN2410L-G-P014:	N-Channel Enhancement-Mode, Vertical DMOS FET, 3-lead TO-92, 2000/AMMO Pack

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